V depends on the sign of N. When N = 0 we always have  $V \sim V_x$ . This explains why the motion of the normal regions was observed in [8] in indium ( $N \neq 0$ ) but not in tin (N = 0).

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  - 1) For long waves  $\zeta(x = a_n/2) \approx \zeta(x = -a_n/2)$ .

## PRESSURE DEPENDENCE OF ELECTRON EFFECTIVE MASS IN INDIUM ANTIMONIDE

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By changing the width of the forbidden band in a crystal, hydrostatic compression affects the value of the effective mass of the carriers. If the band is non-parabolic, as is the conduction band in InSb, the effective mass varies with the filling of the band, and the pressure can have diverse influences on the effective mass.

According to Kane's theory, the electron effective mass  $m_n$  at the bottom of the conduction band is given by the formula

$$\frac{m_0}{m_n} = 1 + \frac{\epsilon_p}{3} \left( \frac{2}{\epsilon_g} + \frac{1}{\epsilon_g + \Delta} \right) , \qquad (1)$$

where  $\epsilon_{g} = \epsilon(\Gamma_{lc}) - \epsilon(\Gamma_{l5v})$  is the width of the forbidden band at the  $\Gamma$ -point,  $\Delta$  the energy of spin-orbit splitting of the valence band at the  $\Gamma$ -point,  $\epsilon_{p} = (2m_{0}/\hbar^{2}) T^{2}$ , P the matrix element of the interaction between the states  $\Gamma_{lc}$  (conduction band) and  $\Gamma_{l5v}$  (valence band), and  $m_{0}$  the mass of the free electron.

Under the usual assumption that  $\epsilon_p$  is not affected by small changes of the lattice period, the mass m<sub>n</sub> is almost proportional, according to (1), to  $\epsilon_g$ , which in InSb increases linearly with the pressure P with a coefficient  $d\epsilon_g/dP = 1.6 \times 10^{-5} \text{ eV/atm}$ .

We undertook an experimental study of the influence of hydrostatic pressure up to 16.5 katm on the effective mass m of the electrons in InSb at  $T = 96^{\circ}K$ . To this end, we measured the thermal emf and the Hall effect in classically strong magnetic fields, when neither de-